

PNP SILICON DUAL TRANSISTOR

Qualified per MIL-PRF-19500/336

Devices

| | |
|----------------|----------------|
| 2N3810 | 2N3811 |
| 2N3810L | 2N3811L |
| 2N3810U | 2N3811U |

Qualified Level

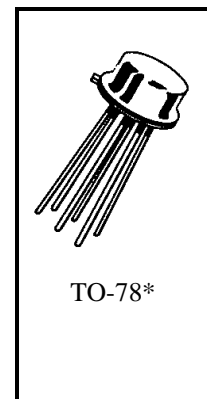
JAN
JANTX
JANTXV

MAXIMUM RATINGS

| Ratings | Symbol | Value | Unit | |
|---|----------------|--------------------------------|----------------------------------|--------------------|
| Collector-Emitter Voltage | V_{CEO} | 60 | Vdc | |
| Collector-Base Voltage | V_{CBO} | 60 | Vdc | |
| Emitter-Base Voltage | V_{EBO} | 5.0 | Vdc | |
| Collector Current | I_C | 50 | mAdc | |
| | | One Section¹ | Both Sections² | |
| Total Power Dissipation @ $T_A = +25^{\circ}\text{C}$ | P_T | 0.5 | 0.6 | W |
| Operating & Storage Junction Temperature Range | T_J, T_{stg} | -65 to +200 | | $^{\circ}\text{C}$ |

1) Derate linearly 2.86 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$

2) Derate linearly 3.43 mW/ $^{\circ}\text{C}$ for $T_A > +25^{\circ}\text{C}$



*See appendix A for package outline

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

| Characteristics | Symbol | Min. | Max. | Unit |
|-----------------|--------|------|------|------|
|-----------------|--------|------|------|------|

OFF CHARACTERISTICS

| | | | | |
|---|---------------|-----|----|------------------|
| Collector-Base Breakdown Voltage $I_C = 10 \mu\text{Adc}$ | $V_{(BR)CBO}$ | 60 | | Vdc |
| Collector-Emitter Breakdown Current $I_C = 10 \text{mAdc}$ | $V_{(BR)CEO}$ | 60 | | Vdc |
| Emitter-Base Breakdown Voltage $I_E = 10 \mu\text{Adc}$ | $V_{(BR)EBO}$ | 5.0 | | Vdc |
| Collector-Base Cutoff Current $V_{CB} = 50 \text{Vdc}$ | I_{CBO} | | 10 | ηAdc |
| Emitter-Base Cutoff Current $V_{EB} = 4.0 \text{Vdc}$ | I_{EBO} | | 10 | ηAdc |

